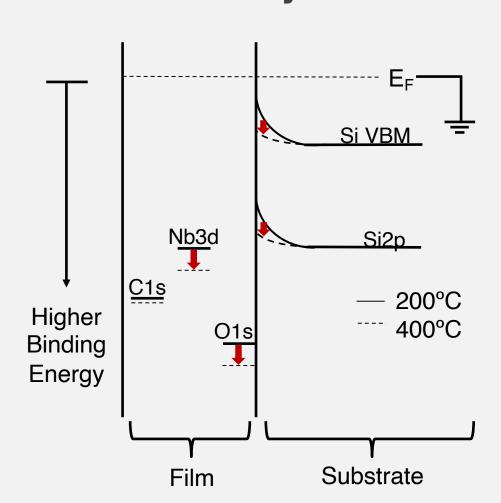


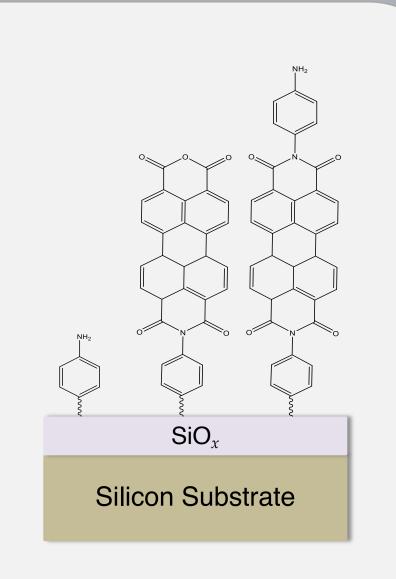
Silanes Ruin Silicon Surfaces, Can We Fix It?

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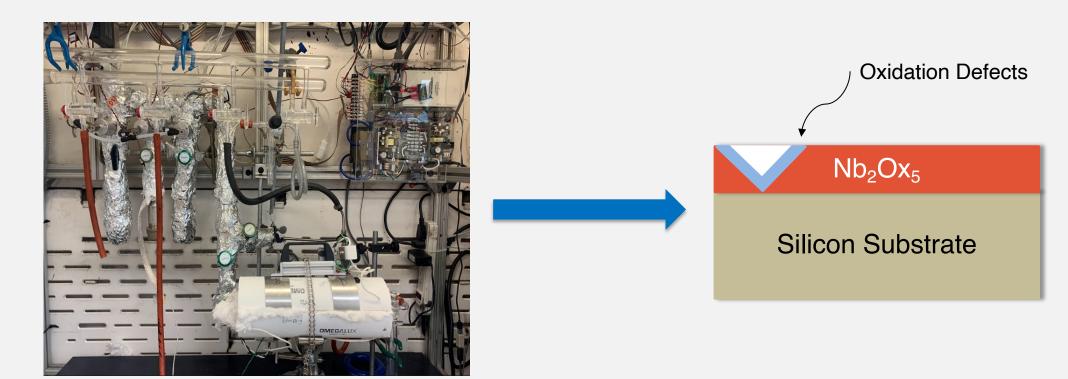
1. Niobium: Why?



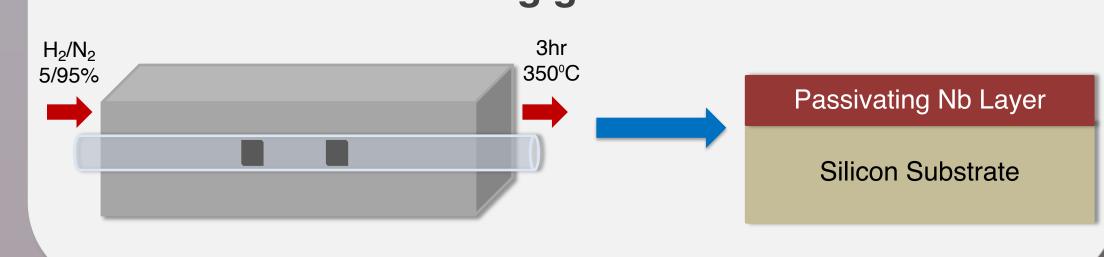


- Nb layers improve Si surface electronics.
- Research question: can Nb minimize surface defects when silanes are attached?

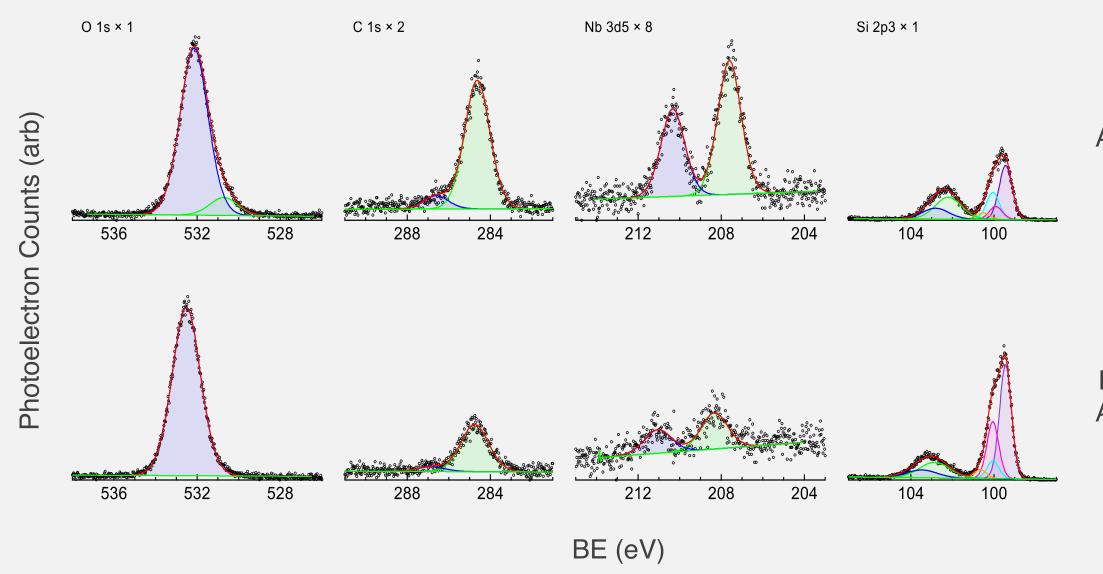
2. ALD Creates Ultrathin Nb₂O₅ on Si...



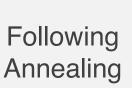
...that forming gas reduces to interfacial Nb

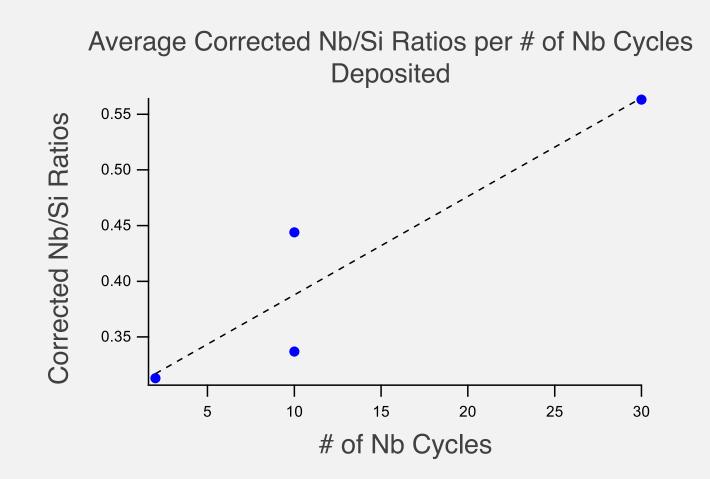


3. XPS Shows Niobium Oxide on Silicon Surfaces



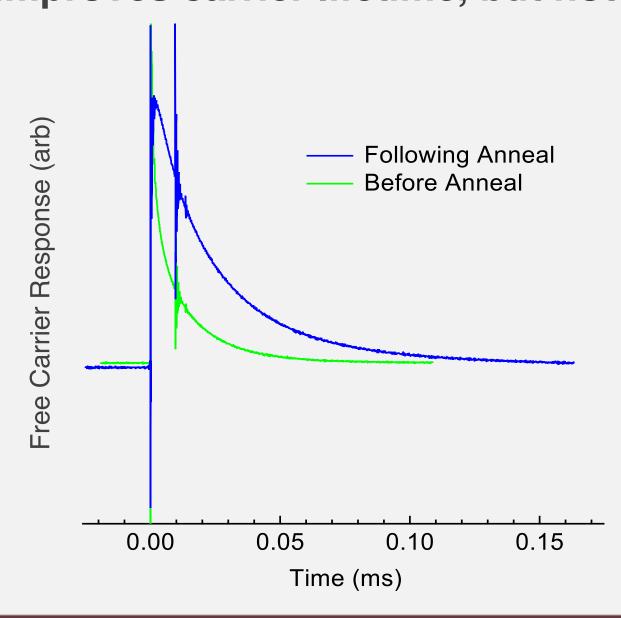
Before Annealing



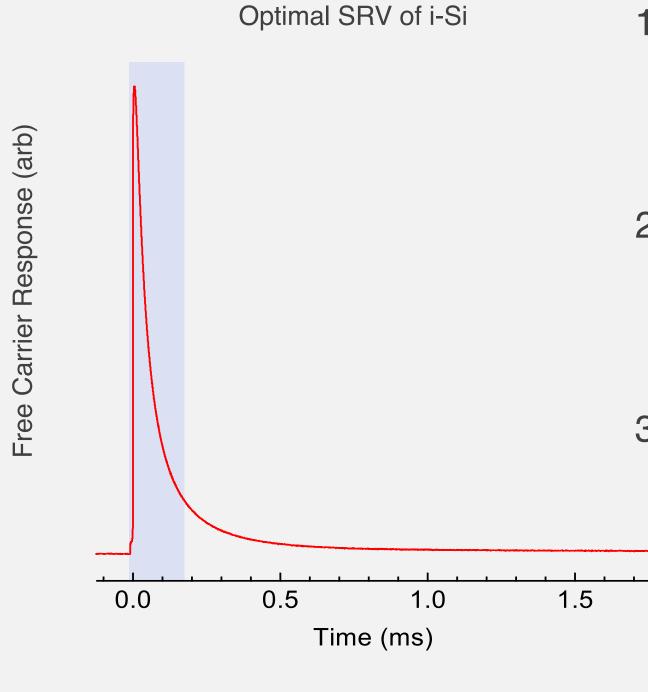


- Change in C and Nb counts show that the annealing recipe needs adjustments
- Increased silicon areas may indicate Nb layer decomposition

4. Microwave Photoconductivity: Annealing Nbon-Si improves carrier lifetime, but not enough



5. Future Approaches and Conclusions



- 1. Optimize annealing by adjusting either temp, time or flow rate
- More data on controlled samples of i-Si with and without silane
- 3. Silane derivatization with different concentrations

Acknowledgments

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Linearity of Nb deposition in the ALD

- SRV values need more consistency
- Silane impact not confirmed...yet

